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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/689,233	10/20/2003	Kia Seng Low	02 P 15173 US / INTECH 3.	4063
48154	7590	12/28/2005		EXAMINER
SLATER & MATSIL LLP 17950 PRESTON ROAD SUITE 1000 DALLAS, TX 75252			SARKAR, ASOK K	
			ART UNIT	PAPER NUMBER
				2891

DATE MAILED: 12/28/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/689,233	LOW ET AL.
	Examiner Asok K. Sarkar	Art Unit 2891

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 29 November 2005.

2a) This action is FINAL. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1,4,7-9,12-16,53,55-60,62,63 and 65-68 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5) Claim(s) _____ is/are allowed.

6) Claim(s) 1,4,7-9,12-16,53,55-60,62,63 and 65-68 is/are rejected.

7) Claim(s) _____ is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on 29 November 2005 is/are: a) accepted or b) objected to by the Examiner.

 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) Paper No(s)/Mail Date. ____ .
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date ____ .
5) Notice of Informal Patent Application (PTO-152)
6) Other: ____ .

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. The factual inquiries set forth in *Graham v. John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

1. Determining the scope and contents of the prior art.
2. Ascertaining the differences between the prior art and the claims at issue.
3. Resolving the level of ordinary skill in the pertinent art.
4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

3. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

4. Claims 1, 4, 8, 9, 12 – 14, 16, 53, 55, 57, 58, 60, 63, 65, 66 and 68 are rejected under 35 U.S.C. 103(a) as being unpatentable over Boeck, US 5,880,018.

Regarding claims 1, 13, 53, 60 and 63, Boeck teaches a method of incorporating a first dielectric material into a layer of an electronic structure that includes at least one conductive line of a semiconductor device, said layer of electronic structure and said at least one conductive line being fabricated by a process that includes at least one thermal processing step at a temperature greater than a maximum withstand temperature of said dielectric material, said method comprising:

- fabricating said layer of electronic structure and said at least one conductive line 14 and 20 at least through the thermal processing step, said layer comprising a second dielectric material 20 formed atop an etch stop layer 16 and lying adjacent said at least one conductive line and said second dielectric material having a maximum withstand temperature greater than the temperature of the thermal processing step with reference to Fig. 3; Boeck teaches first dielectric material 22 has a lower dielectric constant than the second dielectric material in column 4, lines 45 – 67.
- removing at least a portion of said second dielectric material from said layer down to said etch stop layer with reference to Fig. 4 ; and
- depositing a layer of said first dielectric material 22 in place of the removed portion of said second dielectric material with reference to Fig. 5 in between column 3, line 10 and column 4, line 67.

Boeck teaches contact barrier layer 49 for the conductive lines in column 6, line 27 with reference to Fig. 10, but fails to teach removing the second dielectric layer subsequent to thermal processing step.

However, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Boeck and apply a thermal processing step such as anneal the barrier layer since annealing is conventional for the benefit of making the layer pinholes free for providing proper barrier function.

Regarding claims 8, 16, 57 and 68, Boeck teaches the step of depositing a layer of said first dielectric material includes depositing said layer atop said conductive line; and planarizing said layer of said first dielectric material such that a portion thereof remains atop said conductive line and serves as an inter – level dielectric layer with reference to Fig. 6 and in column 4, lines 45 – 67.

Regarding claim 9, Boeck teaches a method of incorporating a first dielectric material into an insulator structure that is adjacent to at least one conductive line of a semiconductor device said insulator structure and said at least one conductive line being fabricated by a process that includes at least one thermal processing step at a temperature- greater than a maximum withstand temperature of said first dielectric material, said method comprising:

fabricating said insulator structure and said at least one conductive line at least through the thermal processing step using a second dielectric material with a maximum withstand temperature greater than the temperature of the thermal processing step, said fabricating step comprising:

- depositing a first layer of said second dielectric material 12 atop a surface of a

semiconductor substrate (see Fig. 1); Boeck teaches first dielectric material 22 has a lower dielectric constant than the second dielectric material in column 4, lines 45 – 67.

- planarizing said first layer of said second dielectric material 12 to a top-surface of another conductive line disposed atop said semiconductor substrate,
- depositing another layer of said second dielectric material 18 atop said first layer of said second dielectric material 12 and atop said another conductive line (see Fig. 1),
- patterning and etching said another layer of said second dielectric material to form at least one opening therein (see Fig. 2), and
- filling said opening with at least one conductive material 14 and 20 to form said at least one conductive line (see Fig. 3);
- removing at least a portion of said second dielectric material (see Fig. 4), and
- depositing a layer of said first dielectric material 22 in place of the removed portion of said second dielectric material.

Boeck teaches contact barrier layer 49 for the conductive lines in column 6, line 27 with reference to Fig. 10, but fails to teach removing the second dielectric layer subsequent to thermal processing step.

However, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Boeck and apply a thermal processing step such as anneal the barrier layer since annealing is conventional for the benefit of making the layer pinholes free for providing proper barrier function.

Regarding claims 4, 12, 14, 55, 58, 62, 65 and 66 especially claim 58, Boeck teaches all limitations as were described earlier in rejecting claims 1, 53 and 60 and using contact barrier layer 49 in column 6, line 27 with reference to Fig. 10, but fails to teach annealing of the barrier layer at a temperature greater than the maximum withstand temperature of the first dielectric material and removing the second dielectric layer subsequent to thermal processing step..

However, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Boeck and anneal the barrier layer since annealing is conventional for the benefit of making the layer pinholes free for providing proper barrier function and the annealing temperature will also be greater than the maximum withstand temperature of the first dielectric material since the melting temperature of the low – k dielectric materials are quite low.

Regarding claims 14 and 66, Boeck fails to teach a timed etching step for the dielectric material.

However, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify the etching step by applying a timed etching to stop the etching at a time when the etching reaches the conductive plugs.

5. Claims 7, 15, 56, 59 and 67 are rejected under 35 U.S.C. 103(a) as being unpatentable over Boeck, US 5,880,018 in view of Seta, US 2002/0102843.

Regarding these claims, especially 59, Boeck teaches all limitations as were described earlier in rejecting claims 1, 53 and 60. Boeck also teaches planarizing the layer of first dielectric material to a top surface of the conductive line with reference

to Fig. 6, and teaches that process steps can be repeated in order to form another sets of interconnects overlying one conductive interconnect to form multiple layer interconnects but fails to teach depositing another layer of the first dielectric material atop said layer of planarized dielectric material and atop said conductive line.

Seta teaches that a two layer interconnect can be formed by depositing another layer of the first dielectric material 116 atop the layer of planarized dielectric material 116 and atop said conductive line 110 with reference to Fig. 34A for the benefit of forming interconnects with height differences in a two layer structure in paragraph 352.

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Boeck and deposit another layer of the first dielectric material atop said layer of planarized dielectric material and atop said conductive line for the benefit of forming interconnects with height differences in a two layer structure as taught by Seta in paragraph 352.

Response to Arguments

6. Applicant's arguments filed November 29, 2005 have been fully considered but they are not persuasive. The Applicant's primary argument is regarding the absence of any teaching about thermal processing step by Boeck (see paragraphs 2 – 4 starting on page 12 of the amendment). This argument is not persuasive because of the following reasons. Boeck recites the main manufacturing steps omitting the obvious thermal processing steps. For example, the deposition of dielectric materials is carried out at certain temperatures, which are generally above room temperatures. The second dielectric layer, which is a silicon dioxide layer, usually is annealed for densification.

The densification is necessary for etching a via or trench through the dielectric layer.

Thus, although Boeck is silent about the thermal processing steps, it would have been obvious to one with ordinary skill in the art at the time of the invention to incorporate various thermal processing steps as routine and standard processing steps during a semiconductor device manufacturing process as defined and disclosed by Boeck as were described earlier in rejecting the claims.

Conclusion

7. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Asok K. Sarkar whose telephone number is 571 272 1970. The examiner can normally be reached on Monday - Friday (8 AM- 5 PM).

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, William B. Baumeister can be reached on 571 272 1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

9. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Asok K. Sarkar

Asok K. Sarkar
December 22, 2005

Primary Examiner